What is claimed is

1. A method of forming a single sided conductor, comprising:

providing a substrate having an opening, said opening exposing a sidewall and an opening base surface;

forming a tilted mask layer in said opening, said tilted mask layer exposing said sidewall and a portion of said opening base surface; and

forming a dielectric layer on said exposed sidewall and said exposed opening base surface.

2. The method of claim 1, wherein said step of forming said tilted mask layer comprises:

coating a layer of photoresist over said substrate;

removing a portion of said photoresist such that said opening is partially filled with said photoresist; and

tilting said substrate to reflow said photoresist layer to form said tilted mask layer in said opening.

3. The method of claim 2, wherein said substrate is heated during the reflow of said photoresist layer.

4. The method of claim 3, wherein said substrate is heated to a temperature about 100 to 150℃ for about 100-150 seconds.

5. The method of claim 2, further comprising a step of hardening said photoresist layer by ultraviolet after said photoresist layer is reflowed.

6. The method of claim 1, further comprising an ozone ashing step before said dielectric layer is formed.

7. The method of claim 1, wherein a native oxide layer is grown on sad exposed sidewall and said exposed opening base surface before said dielectric layer is formed.

8. The method of claim 7, wherein said dielectric layer is an oxide layer formed by

liquid phase deposition.

9. The method of claim 1, further comprising a step of stripping said tilted mask layer.

10. The method of claim 9, wherein a conductive layer is formed over said substrate after said tilted mask layer is stripped.

11. A method of forming a semiconductor device having a single sided conductor, comprising:

providing a semiconductor substrate having a pad dielectric layer thereon, a storage node therein, and an opening etched therein, said opening exposing a sidewall and a surface of said storage node;

coating a layer of photoresist on said pad dielectric layer;

removing a portion of said photoresist such that said opening is partially filled with said photoresist;

tilting said semiconductor substrate to reflow said photoresist layer to form a tilted photoresist layer in said opening, said tilted photoresist layer exposing said sidewall and a portion of said surface of said storage node;

forming a dielectric layer on said exposed sidewall and said exposed surface;

removing said tilted photoresist; and

forming a conductive layer over said semiconductor substrate.

12. The method of claim 11, wherein said semiconductor substrate is heated during the reflow of said photoresist layer.

13. The method of claim 12, wherein said semiconductor substrate is heated to a temperature about 100 to 150℃ for about 100-150 seconds.

14. The method of claim 11, further comprising a step of hardening said photoresist layer by ultraviolet after said photoresist layer is reflowed.

15. The method of claim 11, further comprising a step of ozone ashing before said

dielectric layer is formed.

16. The method of claim 11, wherein a native oxide layer is grown on sad exposed sidewall and said exposed surface of said storage node before said dielectric layer is formed.

17. The method of claim 16, wherein said dielectric layer is an oxide layer formed by liquid phase deposition.